Woojin Jeon

List of Publications by Year
in descending order

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		394286	276775
62	1,775	19	41
papers	citations	h-index	g-index

63	63	63	2314
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Grain size engineering for ferroelectric Hf0.5Zr0.5O2 films by an insertion of Al2O3 interlayer. Applied Physics Letters, 2014, 105, .	1.5	187
2	Highly Improved Uniformity in the Resistive Switching Parameters of TiO₂ Thin Films by Inserting Ru Nanodots. Advanced Materials, 2013, 25, 1987-1992.	11.1	170
3	32 Ã— 32 Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory. Advanced Functional Materials, 2013, 23, 1440-1449.	7.8	152
4	Ferroelectric properties and switching endurance of Hf_{0.5}Zr_{0.5}O₂ films on TiN bottom and TiN or RuO₂ top electrodes. Physica Status Solidi - Rapid Research Letters, 2014, 8, 532-535.	1.2	131
5	High-concentration boron doping of graphene nanoplatelets by simple thermal annealing and their supercapacitive properties. Scientific Reports, 2015, 5, 9817.	1.6	116
6	Atomic Layer Deposition of SrTiO₃ Films with Cyclopentadienyl-Based Precursors for Metalâ€“Insulatorâ€“Metal Capacitors. Chemistry of Materials, 2013, 25, 953-961.	3.2	69
7	Titanium dioxide thin films for next-generation memory devices. Journal of Materials Research, 2013, 28, 313-325.	1.2	67
8	Structure and Electrical Properties of Al-Doped HfO₂ and ZrO₂ Films Grown via Atomic Layer Deposition on Mo Electrodes. ACS Applied Materials & Interfaces, 2014, 6, 22474-22482.	4.0	63
9	Waferâ€Scale Synthesis of Reliable Highâ€Mobility Molybdenum Disulfide Thin Films via Inhibitorâ€Utilizing Atomic Layer Deposition. Advanced Materials, 2017, 29, 1703031.	11.1	56
10	Recent advances in the understanding of high-kdielectric materials deposited by atomic layer deposition for dynamic random-access memory capacitor applications. Journal of Materials Research, 2020, 35, 775-794.	1.2	55
11	Frustration of Negative Capacitance in Al2O3/BaTiO3 Bilayer Structure. Scientific Reports, 2016, 6, 19039.	1.6	44
12	TiO[sub 2]âˆ•Al[sub 2]O[sub 3]âˆ•TiO[sub 2] Nanolaminated Thin Films for DRAM Capacitor Deposited by Plasma-Enhanced Atomic Layer Deposition. Electrochemical and Solid-State Letters, 2008, 11, H19.	2.2	41
13	Improved Initial Growth Behavior of SrO and SrTiO₃ Films Grown by Atomic Layer Deposition Using {Sr(demamp)(tmhd)}₂ as Sr-Precursor. Chemistry of Materials, 2015, 27, 3881-3891.	3.2	32
14	Evaluating the Top Electrode Material for Achieving an Equivalent Oxide Thickness Smaller than 0.4 nm from an Al-Doped TiO₂ Film. ACS Applied Materials & Interfaces, 2014, 6, 21632-21637.	4.0	31
15	Interfacial charge-induced polarization switching in Al2O3/Pb(Zr,Ti)O3 bi-layer. Journal of Applied Physics, 2015, 118, .	1.1	30
16	Growth of Conductive SrRuO₃ Films by Combining Atomic Layer Deposited SrO and Chemical Vapor Deposited RuO₂ Layers. Chemistry of Materials, 2012, 24, 4686-4692.	3.2	26
17	High-throughput fabrication of infinitely long 10 nm slit arrays for terahertz applications. Journal of Infrared, Millimeter, and Terahertz Waves, 2015, 36, 262-268.	1.2	26
18	Vapor Transport Synthesis of Two-Dimensional SnS₂ Nanocrystals Using a SnS₂ Precursor Obtained from the Sulfurization of SnO₂. Crystal Growth and Design, 2016, 16, 3884-3889.	1.4	23

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19	Controlling the Electrical Characteristics of ZrO₂/Al₂O₃/ZrO₂ Capacitors by Adopting a Ru Top Electrode Grown via Atomic Layer Deposition. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800454.	1.2	23
20	Controlling the Al-Doping Profile and Accompanying Electrical Properties of Rutile-Phased TiO₂ Thin Films. ACS Applied Materials & Interfaces, 2014, 6, 7910-7917.	4.0	21
21	Improved performance and stability of In-Sn-Zn-O thin film transistor by introducing a meso-crystalline ZrO2 high-k gate insulator. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	0.9	20
22	Controlling the initial growth behavior of SrTiO3 films by interposing Al2O3 layers between the film and the Ru substrate. Journal of Materials Chemistry, 2012, 22, 15037.	6.7	19
23	Mesostructured Hf_xAl_yO₂ Thin Films as Reliable and Robust Gate Dielectrics with Tunable Dielectric Constants for High-Performance Graphene-Based Transistors. ACS Nano, 2016, 10, 6659-6666.	7.3	19
24	The impact of plasma-enhanced atomic layer deposited ZrSiOx insulators on low voltage operated In-Sn-Zn-O thin film transistors. Ceramics International, 2019, 45, 19166-19172.	2.3	19
25	Impact of Bimetal Electrodes on Dielectric Properties of TiO₂ and Al-Doped TiO₂ Films. ACS Applied Materials & Interfaces, 2012, 4, 4726-4730.	4.0	18
26	One-Dimensional TiO2@Ag Nanoarchitectures with Interface-Mediated Implementation of Resistance-Switching Behavior in Polymer Nanocomposites. ACS Applied Materials & Interfaces, 2012, 4, 5727-5731.	4.0	18
27	Chemistry of active oxygen in RuO_x and its influence on the atomic layer deposition of TiO₂ films. Journal of Materials Chemistry C, 2014, 2, 9993-10001.	2.7	18
28	Demonstrating the Ultrathin Metalâ€“Insulatorâ€“ Metal Diode Using TiN/ZrO₂â€“Al₂O₃â€“ZrO₂Stack by Employing RuO₂Top Electrode. IEEE Transactions on Electron Devices, 2018, 65, 660-666.	1.6	17
29	Atomic layer deposition of Ru thin films using (2,4-dimethyloxopentadienyl)(ethylcyclopentadienyl)Ru and the effect of ammonia treatment during the deposition. Journal of Materials Chemistry C, 2020, 8, 6993-7004.	2.7	17
30	Electrical Properties of ZrO₂/Al₂O₃/ZrO₂â€Based Capacitors with TiN, Ru, and TiN/Ru Top Electrode Materials. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800356.	1.2	16
31	Physisorbed-precursor-assisted atomic layer deposition of reliable ultrathin dielectric films on inert graphene surfaces for low-power electronics. 2D Materials, 2016, 3, 035027.	2.0	15
32	Quantitative Analysis of the Incorporation Behaviors of Sr and Ti Atoms During the Atomic Layer Deposition of SrTiO₃ Thin Films. ACS Applied Materials & Interfaces, 2018, 10, 8836-8844.	4.0	15
33	A visible-light phototransistor based on the heterostructure of ZnO and TiO₂ with trap-assisted photocurrent generation. RSC Advances, 2021, 11, 12051-12057.	1.7	15
34	Modulated filamentary conduction of Ag/TiO2 core-shell nanowires to impart extremely sustained resistance switching behavior in a flexible composite. Applied Materials Today, 2020, 19, 100569.	2.3	12
35	Y-doped HfO2 deposited by atomic layer deposition using a cocktail precursor for DRAM capacitor dielectric application. Ceramics International, 2022, 48, 3236-3242.	2.3	11
36	Asymmetry in electrical properties of Alâ€doped TiO₂ film with respect to bias voltage. Physica Status Solidi - Rapid Research Letters, 2015, 9, 410-413.	1.2	10

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37	Controlling the Current Conduction Asymmetry of HfO₂ Metalâ€“Insulatorâ€“Metal Diodes by Interposing Al₂O₃ Layer. IEEE Transactions on Electron Devices, 2019, 66, 402-406.	1.6	10
38	Improving the photodetection and stability of a visible-light QDs/ZnO phototransistor via an Al₂O₃ additional layer. Journal of Materials Chemistry C, 2021, 9, 2550-2560.	2.7	10
39	Optimization of Chemical Structure of Schottky-Type Selection Diode for Crossbar Resistive Memory. ACS Applied Materials & Interfaces, 2012, 4, 5338-5345.	4.0	9
40	Reducing the nano-scale defect formation of atomic-layer-deposited SrTiO3 films by adjusting the cooling rate of the crystallization annealing of the seed layer. Thin Solid Films, 2015, 589, 723-729.	0.8	9
41	Chemistry of SiNx thin film deposited by plasma-enhanced atomic layer deposition using di-isopropylaminosilane (DIPAS) and N2 plasma. Ceramics International, 2018, 44, 20890-20895.	2.3	9
42	Scaling the Equivalent Oxide Thickness by Employing a TiO₂ Thin Film on a ZrO₂â€“Al₂O₃â€Based Dielectric for Further Scaling of Dynamic Random Access Memory. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900282.	1.2	9
43	Improving the photoresponsivity and reducing the persistent photocurrent effect of visible-light ZnO/quantum-dot phototransistors via a TiO₂ layer. Journal of Materials Chemistry C, 2020, 8, 16384-16391.	2.7	9
44	Nanoscale surface engineering of a high-k ZrO₂/SiO₂ gate insulator for a high performance ITZO TFT via plasma-enhanced atomic layer deposition. Journal of Materials Chemistry C, 2020, 8, 13342-13348.	2.7	9
45	Modulation of the adsorption chemistry of a precursor in atomic layer deposition to enhance the growth per cycle of a TiO₂ thin film. Physical Chemistry Chemical Physics, 2021, 23, 2568-2574.	1.3	9
46	Substrate Effects on the Growth Behavior of Atomic-Layer-Deposited Ru Thin Films Using RuO₄ Precursor and N₂/H₂ Mixed Gas. Journal of Physical Chemistry C, 2019, 123, 22539-22549.	1.5	8
47	Improved Properties of the Atomic Layer Deposited Ru Electrode for Dynamic Random-Access Memory Capacitor Using Discrete Feeding Method. ACS Applied Materials & Interfaces, 2021, 13, 23915-23927.	4.0	7
48	The Significance on Structural Modulation of Buffer and Gate Insulator for ALD Based InGaZnO TFT Applications. IEEE Transactions on Electron Devices, 2021, 68, 6147-6153.	1.6	7
49	Highly sustainable mechanical/electrical resistance switching behaviors via one-dimensional Ag/TiO2 core-shell resistive switchable materials in flexible composite. Organic Electronics, 2021, 88, 105968.	1.4	6
50	Optimized Al-doped TiO₂ gate insulator for a metal-oxide-semiconductor capacitor on a Ge substrate. Journal of Materials Chemistry C, 2021, 9, 1572-1583.	2.7	6
51	Optimization of a SiOx/SiNxOyCz multilayer structure for a reliable gas diffusion barrier via low-temperature plasma-enhanced atomic layer deposition. Ceramics International, 2019, 45, 7407-7412.	2.3	5
52	Sustainable resistance switching performance from composite-type ReRAM device based on carbon Nanotube@Titania coreâ€“shell wires. Scientific Reports, 2020, 10, 18830.	1.6	4
53	Investigating the interface characteristics of high-k ZrO2/SiO2 stacked gate insulator grown by plasma-enhanced atomic layer deposition for improving the performance of InSnZnO thin film transistors. AIP Advances, 2020, 10, .	0.6	4
54	An Empirical Investigation on the Effect of Oxygen Vacancy in ZrO₂ Thin Film on the Frequency-Dependent Capacitance Degradation in the Metalâ€“Insulatorâ€“Metal Capacitor. IEEE Transactions on Electron Devices, 2021, 68, 5753-5757.	1.6	4

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55	Chemistry of ruthenium as an electrode for metalâ€“insulatorâ€“metal capacitor application. Nanotechnology, 2021, 32, 045201.	1.3	4
56	Controlling the crystallinity of HfO2 thin film using the surface energy-driven phase stabilization and template effect. Applied Surface Science, 2022, 590, 153082.	3.1	4
57	An Al-doped TiO₂ interfacial layer for effective hole injection characteristics of quantum-dot light-emitting diodes. Journal of Materials Chemistry C, 2022, 10, 7294-7303.	2.7	4
58	Resistive Memory: 32 Ã— 32 Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory (Adv. Funct. Mater. 11/2013). Advanced Functional Materials, 2013, 23, 1350-1350.	7.8	2
59	Depletion effect of polycrystalline-silicon gate electrode by phosphorus deactivation. Solid-State Electronics, 2017, 127, 1-4.	0.8	2
60	Resistance Switching Capable Polymer Nanocomposites Employing Networks of One-Dimensional Nanocarbon Wrapped by TiO2 Conformal Layer. IEEE Nanotechnology Magazine, 2018, 17, 567-573.	1.1	1
61	Comparative Study on the Gateâ€Induced Electrical Instability of pâ€Type SnO Thinâ€Film Transistors with SiO₂ and Al₂O₃/SiO₂ Gate Dielectrics. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000304.	1.2	1
62	Achieving high dielectric constants in tetragonal singleâ€phase ZrHfO ₂ thin films through the atomic layer deposition process using a mixed precursor. Physica Status Solidi (A) Applications and Materials Science, 0, , .	0.8	1